

2N3055 Silicon NPN Power Transistor Audio Power Amp, Medium Speed Switch TO-3 Type Package

Description:

The 2N3055 is a silicon NPN transistor in a TO3 type case designed for general purpose switching and amplifier applications.

Features:

- DC Current Gain: h_{FE} = 20 70 @ l_C = 4A
- Collector-Emitter Saturation Voltage: $V_{CE(sat)} = 1.1V$ (Max) @ $I_C = 4A$
- Excellent Safe Operating Area

Absolute Maximum Ratings:

Collector–Emitter Voltage, V _{CEO}	60V
Collector–Emitter Voltage, V _{CER}	70V
Collector-Base Voltage, V _{CB}	
Emitter-Base Voltage, V _{EB}	
Continuous Collector Current, I _C	15A
Base Current, I _B	7A
Total Device Dissipation (T _C = +25°C), P _D	115W
Derate Above 25°C	0.657W/°C
Operating Junction Temperature Range, T _J 65°	' to +200°C
Storage Temperature Range, T _{stq} 65°	' to +200°C
Thermal Resistance, Junction-to-Case, R _{thJC}	

Note 1. Maximum Ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

<u>Electrical Characteristics:</u> (T_C =+25°C unless otherwise specified)

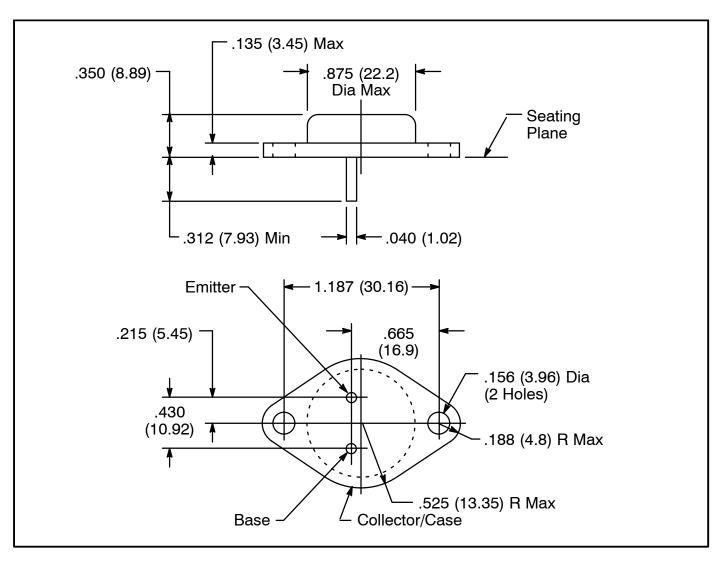
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit			
OFF Characteristics									
Collector-Emitter Sustaining Voltage	V _{CEO(sus)}	I _C = 200mA, I _B = 0, Note 2	60	_	_	V			
Collector-Emitter Sustaining Voltage	V _{CER(sus)}	I_C = 200mA, R_{BE} = 100 Ω , Note 2	70	_	-	V			
Collector Cutoff Current	I _{CEO}	V _{CE} = 30V, I _B = 0	_	_	0.7	mA			
	I _{CEX}	$V_{CE} = 100V, V_{BE(off)} = 1.5V$	-	_	1.0	mA			
		$V_{CE} = 100V, V_{BE(off)} = 1.5V, T_{C} = +150$ °C	_	_	5.0	mA			
Emitter Cutoff Current	I _{EBO}	$V_{BE} = 7V, I_{C} = 0$	-	_	5.0	mA			

Note 2. Pulse Test: Pulse Width ≤ 300µs. Duty Cycle ≤ 2%.

<u>Electrical Characteristics (Cont'd):</u> (T_C =+25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit			
ON Characteristics (Note 2)									
DC Current Gain	h _{FE}	I _C = 4A, V _{CE} = 4V	20	_	70				
		I _C = 10A, V _{CE} = 4V	5	_	_				
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 4A, I _B = 400mA	-	_	1.1	V			
		I _C = 10A, I _B = 3.3A	-	_	3.0	V			
Base-Emitter ON Voltage	V _{BE(on)}	I _C = 4A, V _{CE} = 4V	-	_	1.5	V			
Second Breakdown									
Second Breakdown Collector Current with Base Forward Biased	I _{s/b}	V _{CE} = 40V, t = 1.0s; Nonrepetitive	2.87	_	_	Α			
Dynamic Characteristics									
Current Gain-Bandwidth Product	f _T	I _C = 500mA, V _{CE} = 10V, f = 1MHz	2.5	_	_	MHz			
Small-Signal Current Gain	h _{fe}	$I_C = 1A$, $V_{CE} = 4V$, $f = 1kHz$	15	_	120				
Small-Signal Current Gain Cutoff Frequency	f _{hfe}	V _{CE} = 4V, I _C = 1A, f = 1kHz	10	_	_	kHz			

Note 2. Pulse Test: Pulse Width $\leq 300 \mu s$. Duty Cycle $\leq 2\%$.



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by NTE manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460

2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 2N2369ADCSM

2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E

US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E

NJL0302DG TTA1452B,S4X(S 2N3583 NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13 NTE15 NTE16001 NTE16006

NTE26